Page 1 of 1

## **Form PTO-1449**

## INFORMATION DISCLOSURE STATEMENT

P70853US0 Attorney Docket: Application No.: 10/554,048 October 24, 2005 Filing Date: DOBSCHAL et al. Inventor: Art Unit: Not Yet Assigned Examiner: Not Yet Assigned

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FP	AK	IMADA S ET AL; "Epitaxial Growth of Ferroelectric YMnO <sub>3</sub> thin films on Si (111) Substrates by Molecular Beam Epitaxy"; Japanese Journal of Applied Physics; Publication Office Japanese Journal of Applied Physics; December 1998; pgs. 6497-6501; vol. 37 no. 12A Part 1; Tokyo.					
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